Saulius Marcinkevicius

List of Publications by Year
in descending order

60 papers	1,153 citations	304743 22 h-index	414414 32 g-index
61 all docs	61 docs citations	61 times ranked	1122 citing authors

#	Article	IF	Citations
1	Optimization of InGaN quantum well interfaces for fast interwell carrier transport and low nonradiative recombination. , 2022, , .		2
2	Photon Walk in Transparent Wood: Scattering and Absorption in Hierarchically Structured Materials. Advanced Optical Materials, 2022, 10, .	7.3	8
3	Electron-phonon scattering in <i>Î²</i> -Ga2O3 studied by ultrafast transmission spectroscopy. Applied Physics Letters, 2021, 118, .	3.3	3
4	High internal quantum efficiency of long wavelength InGaN quantum wells. Applied Physics Letters, 2021, 119, .	3.3	10
5	Ultrafast dynamics of hole self-localization in <i>Î²</i> -Ga2O3. Applied Physics Letters, 2020, 116, .	3.3	21
6	Low-temperature carrier transport across InGaN multiple quantum wells: Evidence of ballistic hole transport. Physical Review B, 2020, 101, .	3.2	6
7	Variations of light emission and carrier dynamics around V-defects in InGaN quantum wells. Journal of Applied Physics, 2020, 128, 225703.	2.5	8
8	Optimization of barrier height in InGaN quantum wells for rapid interwell carrier transport and low nonradiative recombination. Applied Physics Express, 2020, 13, 122005.	2.4	4
9	Evidence of trap-assisted Auger recombination in low radiative efficiency MBE-grown III-nitride LEDs. Journal of Applied Physics, 2019, 126, .	2.5	30
10	Electrochemical etching of AlGaN for the realization of thin-film devices. Applied Physics Letters, 2019, 115, 182103.	3.3	20
11	Interwell carrier transport in InGaN/(In)GaN multiple quantum wells. Applied Physics Letters, 2019, 114, .	3.3	21
12	Top-Down Fabrication of High Quality Gallium Indium Phosphide Nanopillar/disk Array Structures. , 2019, , .		1
13	Optical absorption edge broadening in thick InGaN layers: Random alloy atomic disorder and growth mode induced fluctuations. Applied Physics Letters, 2018, 112, .	3.3	31
14	Impact of surface morphology on the properties of light emission in InGaN epilayers. Applied Physics Express, 2018, 11, 051004.	2.4	9
15	Direct Measurement of Nanoscale Lateral Carrier Diffusion: Toward Scanning Diffusion Microscopy. ACS Photonics, 2018, 5, 528-534.	6.6	16
16	Multimode Scanning Near-Field Photoluminescence Spectroscopy of InGaN Quantum Wells. , 2018, , .		0
17	Scanning near-field microscopy of carrier lifetimes in m-plane InGaN quantum wells. Applied Physics Letters, 2017, 110, .	3.3	16
18	Polarization-Resolved Near-Field Spectroscopy of Localized States in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>m</mml:mi></mml:math> -Plane <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow><mml:mi>x</mml:mi></mml: ma. Physical Review Applied, 2017, 7, .	3.8	16

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19	Influence of well width fluctuations on recombination properties in semipolar InGaN quantum wells studied by time- and spatially-resolved near-field photoluminescence. Optical Materials Express, 2017, 7, 3116.	3.0	11
20	Intervalley energy of GaN conduction band measured by femtosecond pump-probe spectroscopy. Physical Review B, 2016, 94, .	3.2	21
21	Photoexcited carrier trapping and recombination at Fe centers in GaN. Journal of Applied Physics, 2016, 119, .	2.5	26
22	Iron as a source of efficient Shockley-Read-Hall recombination in GaN. Applied Physics Letters, 2016, 109, .	3.3	64
23	Scanning near-field optical microscopy of AlGaN epitaxial layers. Proceedings of SPIE, 2016, , .	0.8	0
24	Properties of near-field photoluminescence in green emitting single and multiple semipolar (202Â¯1) plane InGaN/GaN quantum wells. Optical Materials Express, 2016, 6, 39.	3.0	6
25	Impact of carrier localization on radiative recombination times in semipolar (202Â¯1) plane InGaN/GaN quantum wells. Applied Physics Letters, 2015, 107, .	3.3	22
26	High spatial uniformity of photoluminescence spectra in semipolar (202Â¯1) plane InGaN/GaN quantum wells. Journal of Applied Physics, 2015, 117, 023111.	2.5	27
27	Spatial variations of optical properties of semipolar InGaN quantum wells. Proceedings of SPIE, 2015, , .	0.8	0
28	Highly polarized photoluminescence and its dynamics in semipolar (202Â¯1Â¯) InGaN/GaN quantum well. Applied Physics Letters, 2014, 104, .	3.3	33
29	Carrier redistribution between different potential sites in semipolar (202Â¯1) InGaN quantum wells studied by near-field photoluminescence. Applied Physics Letters, 2014, 105, .	3.3	17
30	Optical properties and carrier dynamics in m -plane InGaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 690-693.	0.8	10
31	High spectral uniformity of AlGaN with a high Al content evidenced by scanning near-field photoluminescence spectroscopy. Applied Physics Letters, 2014, 105, .	3.3	20
32	Optical properties of extended and localized states in <i>m</i>-plane InGaN quantum wells. Applied Physics Letters, 2013, 102, .	3.3	36
33	Photoexcited carrier recombination in wide <i>m</i>-plane InGaN/GaN quantum wells. Applied Physics Letters, 2013, 103, .	3.3	46
34	Near-field investigation of spatial variations of (202Â¯1Â¯) InGaN quantum well emission spectra. Applied Physics Letters, 2013, 103, 131116.	3.3	26
35	Carrier dynamics and localization in AlInN/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 853-856.	0.8	1
36	Transient photoreflectance of AlInN/GaN heterostructures. AIP Advances, 2012, 2, .	1.3	8

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37	Nanophotonics: A tutorial. , 2012, , .		0
38	Scanning near-field optical spectroscopy of AlGaN epitaxial layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1617-1620.	0.8	4
39	Localization potentials in AlGaN epitaxial films studied by scanning near-field optical spectroscopy. Journal of Applied Physics, 2011, 109, 113516.	2.5	54
40	Dynamics of polarized photoluminescence in m-plane InGaN/GaN quantum wells. Journal of Applied Physics, 2010, 108, 023101.	2.5	27
41	Optical studies of degradation of AlGaN quantum well based deep ultraviolet light emitting diodes. Journal of Applied Physics, 2010, 108, .	2.5	30
42	Carrier localization in m-plane InGaN/GaN quantum wells probed by scanning near field optical spectroscopy. Applied Physics Letters, 2010, 97, 151106.	3.3	40
43	Aging of AlGaN quantum well light emitting diode studied by scanning near-field optical spectroscopy. Applied Physics Letters, 2009, 95, .	3.3	36
44	Time-resolved luminescence studies of proton-implanted GaN. Applied Physics Letters, 2009, 95, .	3.3	35
45	Dynamics of carrier recombination and localization in AlGaN quantum wells studied by time-resolved transmission spectroscopy. Applied Physics Letters, 2009, 95, 091910.	3.3	14
46	Carrier lifetimes in AlGaN quantum wells: electric field and excitonic effects. Journal Physics D: Applied Physics, 2008, 41, 155116.	2.8	14
47	Transient electromagnetically induced transparency in self-assembled quantum dots. Applied Physics Letters, 2008, 92, .	3.3	93
48	Screening dynamics of intrinsic electric field in AlGaN quantum wells. Applied Physics Letters, 2008, 92, .	3.3	25
49	Electron and Hole Capture Cross-Sections of Fe Acceptors in GaN:Fe Epitaxially Grown on Sapphire. Journal of Electronic Materials, 2007, 36, 1621-1624.	2.2	40
50	The Effect of Barrier Composition on the Vertical Carrier Transport and Lasing Properties of 1.55-<tex>$mu hbox m$</tex>Multiple Quantum-Well Structures. IEEE Journal of Quantum Electronics, 2006, 42, 713-724.	1.9	8
51	Ultrafast carrier trapping in Be-doped low-temperature-grown GaAs. Applied Physics Letters, 1999, 75, 3336-3338.	3.3	42
52	Hole distribution in InGaAsP 1.3-Î¼m multiple-quantum-well laser structures with different hole confinement energies. IEEE Journal of Quantum Electronics, 1999, 35, 603-607.	1.9	7
53	Optically detected carrier transport in III/V semiconductor QW structures: experiments, model calculations and applications in fast 1.55 Î¼m laser devices. Applied Physics B: Lasers and Optics, 1998, 66, 1-17.	2.2	29
54	Non-thermal photoexcited electron distributions in non-stoichiometric GaAs. Semiconductor Science and Technology, 1997, 12, 396-400.	2.0	13

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55	Vertical carrier transport in InGaAsP multiple-quantum-well laser structures: effect of p-doping. IEEE Journal of Selected Topics in Quantum Electronics, 1997, 3, 315-319.	2.9	10
56	Carrier Dynamics in InGaAs/GaAs Quantum Dots. Physica Status Solidi (B): Basic Research, 1997, 204, 290-292.	1.5	6
57	Interwell Carrier Distribution in InAlGaAs Quantum Well Laser Structures. Physica Status Solidi (B): Basic Research, 1997, 204, 577-580.	1.5	0
58	Interwell carrier transport in InGaAsP multiple quantum well laser structures. Applied Physics Letters, 1996, 69, 3695-3697.	3.3	30
59	Carrier trapping due to Fe/sup 3+//Fe/sup 2+/ in InP. , 0, , .		0
60	Subpicosecond carrier capture into intermixed InGaAs/GaAs quantum dots. , 0, , .		0